

R-C Thermal Model Parameters

DESCRIPTION

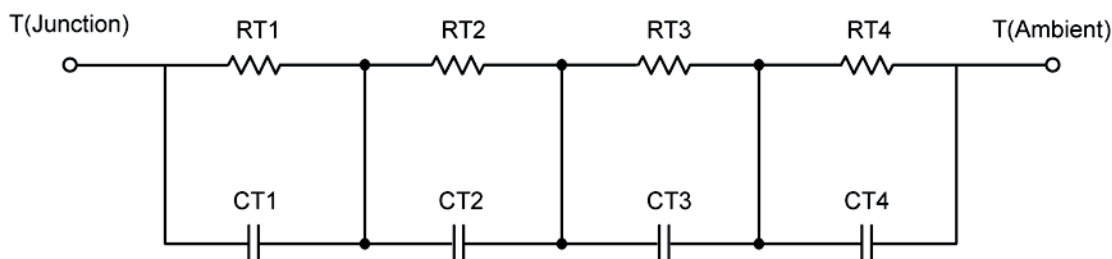
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|--|------------|------|------------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | 6.5905 | N/A | 12.8476 |
| RT2 | 20.5159 | N/A | 6.6056 |
| RT3 | 18.7424 | N/A | 5.4844 |
| RT4 | 44.1513 | N/A | 15.0625 |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | 249.6930 u | N/A | 1.5733 m |
| CT2 | 21.4094 m | N/A | 179.1601 u |
| CT3 | 1.9557 m | N/A | 111.2770 m |
| CT4 | 1.7424 | N/A | 3.5269 m |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

| Thermal Resistance (°C/W) | | | |
|---------------------------------|------------|------|------------|
| Junction to | Ambient | Case | Foot |
| RF1 | 10.3889 | N/A | 7.6815 |
| RF2 | 20.4038 | N/A | 17.9365 |
| RF3 | 15.8355 | N/A | 10.7215 |
| RF4 | 43.3719 | N/A | 3.6606 |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | 262.5988 u | N/A | 158.5866 u |
| CF2 | 2.0086 m | N/A | 695.4765 u |
| CF3 | 31.0523 m | N/A | 4.1695 m |
| CF4 | 1.7791 | N/A | 133.6149 m |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

